

TOSHIBA POWER TRANSISTOR MODULE SILICON NPN EPITAXIAL TYPE (DARLINGTON POWER TRANSISTOR 4 IN 1)

MP4514

HIGH POWER SWITCHING APPLICATIONS

HAMMER DRIVE, PULSE MOTOR DRIVE AND INDUCTIVE

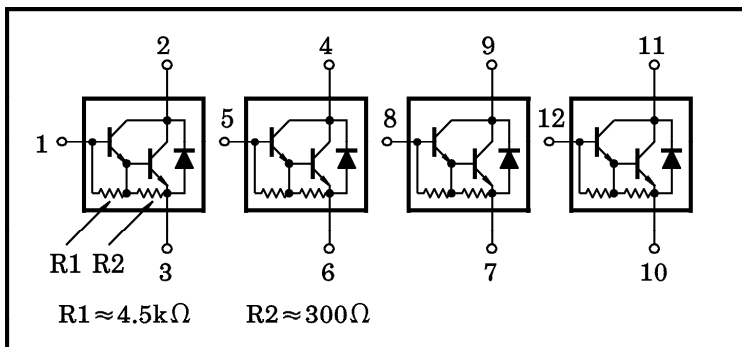
LOAD SWITCHING

- Package with Heat Sink Isolated to Lead (SIP 12 Pin)
- High Collector Power Dissipation (4 Devices Operation)
: $P_T = 5W$ ($T_a = 25^\circ C$)
- High Collector Current : I_C (DC) = 3A (Max.)
- High DC Current Gain : $h_{FE} = 4000$ (Min.) ($V_{CE} = 4V$, $I_C = 1A$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

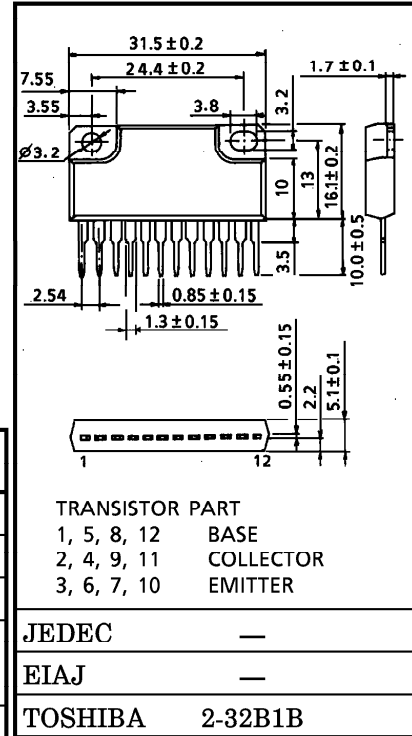
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	120	V
Collector-Emitter Voltage		V_{CEO}	100	V
Emitter-Base Voltage		V_{EBO}	6	V
Collector Current	DC	I_C	3	A
	Pulse	I_{CP}	4	
Continuous Base Current		I_B	0.5	A
Collector Power Dissipation (1 Device Operation)		P_C	3.0	W
Collector Power Dissipation (4 Devices Operation)	$T_a = 25^\circ C$	P_T	5.0	W
	$T_c = 25^\circ C$		25	
Isolation Voltage		V_{Isol}	1000	V
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$

ARRAY CONFIGURATION



INDUSTRIAL APPLICATIONS

Unit in mm



Weight : 6.0g

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THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance of Channel to Ambient (4 Devices Operation, Ta=25°C)	$\Sigma R_{th(j-a)}$	25	°C/W
Thermal Resistance of Channel to Case (4 Devices Operation, Tc=25°C)	$\Sigma R_{th(j-c)}$	5.0	°C/W
Maximum Lead Temperature for Soldering Purposes (3.2mm from Case for 10 Second)	T _L	260	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CBO}	V _{CB} = 120V, I _E = 0	—	—	10	μA
Collector Cut-off Current		I _{CEO}	V _{CE} = 100V, I _B = 0	—	—	10	μA
Emitter Cut-off Current		I _{EBO}	V _{EB} = 6V, I _C = 0	0.5	—	2.5	mA
Collector-Base Breakdown Voltage		V _{(BR)CBO}	I _C = 1mA, I _E = 0	120	—	—	V
Collector-Emitter Breakdown Voltage		V _{(BR)CEO}	I _C = 10mA, I _B = 0	100	—	—	V
DC Current Gain		h _{FE} (1)	V _{CE} = 4V, I _C = 1A	4000	—	15000	
		h _{FE} (2)	V _{CE} = 4V, I _C = 2A	1000	—	—	
Saturation Voltage	Collector-Emitter	V _{CE(sat)}	I _C = 1A, I _B = 1mA	—	—	1.5	V
	Base-Emitter	V _{BE(sat)}	I _C = 1A, I _B = 1mA	—	—	2.0	
Transition Frequency		f _T	V _{CE} = 2V, I _C = 0.5A	—	100	—	MHz
Collector Output Capacitance		C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	20	—	pF
Switching Time	Turn-on Time	t _{on}		—	0.4	—	μs
	Storage Time	t _{stg}		—	4.0	—	
	Fall Time	t _f		IB1 = -IB2 = 1mA, DUTY CYCLE ≤ 1%	—	0.6	

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EMITTER-COLLECTOR DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Current	I_{FM}	—	—	—	2	A
Surge Current	I_{FSM}	t = 1s, 1 shot	—	—	4	A
Forward Voltage	V_F	$I_F = 0.5A, I_B = 0$	—	—	2.0	V
Reverse Recovery Time	t_{rr}	$I_F = 2A, V_{BE} = -3V,$ $dI_F/dt = -50A/\mu s$	—	1.0	—	μs
Reverse Recovery Charge	Q_{rr}		—	5	—	μC

